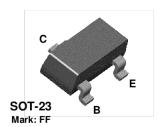


BCV27



NPN Darlington Transistor

This device is designed for applications requiring extremely high current gain at collector currents to 1.0 A. Sourced from Process 05.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	30	V
V _{CBO}	Collector-Base Voltage	40	V
V _{EBO}	Emitter-Base Voltage	10	V
I _C	Collector Current - Continuous	1.2	A
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

 $^{{}^{\}bigstar} \text{These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.}$

These ratings are based on a maximum junction temperature of 150 degrees C.
 These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations

Thermal Characteristics TA = 25 °C unless otherwise noted

Symbol	Characteristic	Max	Units	
		*BCV27		
P _D	Total Device Dissipation Derate above 25°C	350 2.8	mW mW/∘C	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	°C/W	

^{*}Device mounted on FR-4 PCB 40 mm X 40 mm X 1.5 mm.

NPN Darlington Transistor

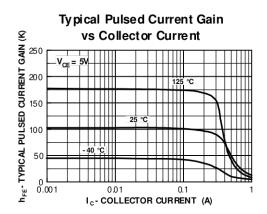
(continued)

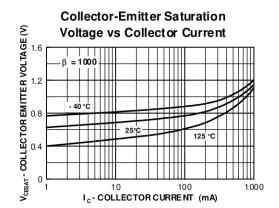
Electrica	I Cha	raatai	dation
Electrica	ii Una	ractei	ISTICS

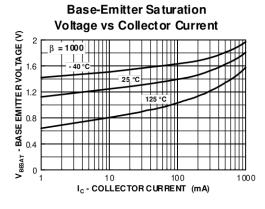
TA = 25°C unless otherwise noted

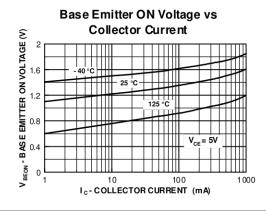
Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
OFF CHA	RACTERISTICS					
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	$I_C = 10 \text{ mA}, I_B = 0$	30			V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_C = 10 \mu A, I_E = 0$	40			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_E = 100 \text{ nA}, I_C = 0$	10			V
I _{CBO}	Collector-Cutoff Current	$V_{CB} = 30 \text{ V}, I_{E} = 0$			0.1	μΑ
I _{EBO}	Emitter-Cutoff Current	$V_{EB} = 10 \text{ V}, I_{C} = 0$			0.1	μА
	ACTERISTICS					
	DC Current Gain	$I_C = 1.0 \text{ mA}, V_{CE} = 5.0 \text{ V}$ $I_C = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}$	4,000 10,000			
1 _{FE}	DC Current Gain	$I_C = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}$ $I_C = 100 \text{ mA}, V_{CE} = 5.0 \text{ V}$	'		1.0	V
V _{CE(sat)}		$I_C = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}$	10,000		1.0	V
T _{CE(sat)}	DC Current Gain Collector-Emitter Saturation Voltage	$\begin{split} I_{C} &= 10 \text{ mA}, \ V_{CE} = 5.0 \text{ V} \\ I_{C} &= 100 \text{ mA}, \ V_{CE} = 5.0 \text{ V} \\ I_{C} &= 100 \text{ mA}, \ I_{B} = 0.1 \text{ mA} \end{split}$	10,000			<u> </u>
V _{CE(sat)}	DC Current Gain Collector-Emitter Saturation Voltage Base-Emitter Saturation Voltage	$\begin{split} I_{C} &= 10 \text{ mA}, \ V_{CE} = 5.0 \text{ V} \\ I_{C} &= 100 \text{ mA}, \ V_{CE} = 5.0 \text{ V} \\ I_{C} &= 100 \text{ mA}, \ I_{B} = 0.1 \text{ mA} \end{split}$	10,000	220		

Typical Characteristics







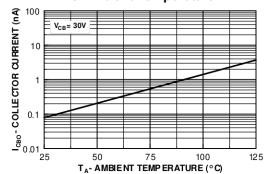


NPN Darlington Transistor

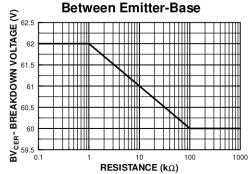
(continued)

Typical Characteristics (continued)

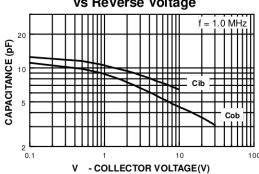
Collector-Cutoff Current vs Ambient Temperature



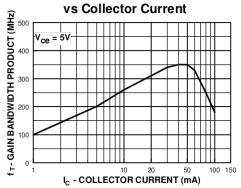
Collector-Emitter Breakdown Voltage with Resistance



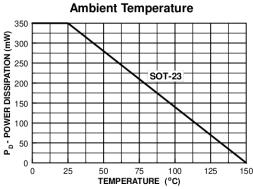
Input and Output Capacitance vs Reverse Voltage

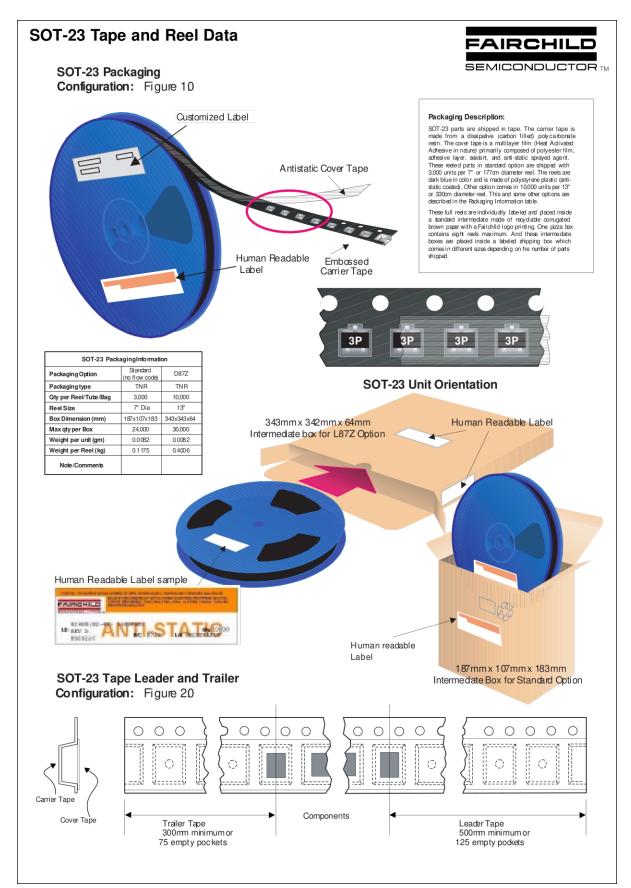


Gain Bandwidth Product



Power Dissipation vs

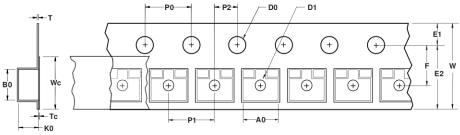




SOT-23 Tape and Reel Data, continued

SOT-23 Embossed Carrier Tape

Configuration: Figure 3.0



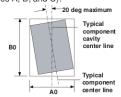
User Direction of Feed

	Dimensions are in millimeter													
Pkg type	Pkg type A0 B0 W D0 D1 E1 E2 F P1 P0 K0 T Wc Tc								Тс					
SOT-23 (8mm)	3.15 +/-0.10	2.77 +/-0.10	8.0 +/-0.3	1.55 +/-0.05	1.125 +/-0.125	1.75 +/-0.10	6.25 min	3.50 +/-0.05	4.0 +/-0.1	4.0 +/-0.1	1.30 +/-0.10	0.228 +/-0.013	5.2 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation



Sketch B (Top View)
Component Rotation



Sketch C (Top View)
Component lateral movement

SOT-23 Reel Configuration: Figure 4.0

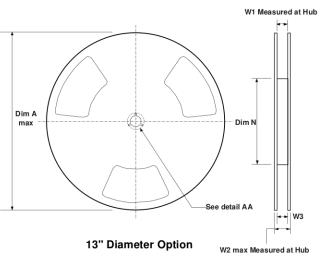
Reel Option

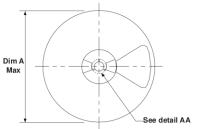
7" Dia 13" Dia Dim A

0.059 1.5

Tape Size

8mm





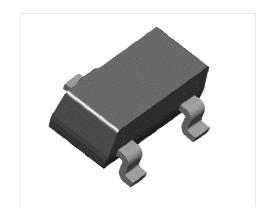
7" Diameter Option B Min Dim C

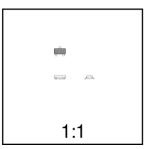
DETAIL AA

Dimensions are in inches and millimeters							
Dim C Dim D Dim		Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)		
512 +0.020/-0.008	0.795	2.165	0.331 +0.059/-0.000	0.567	0.311 - 0.429		
13 +0.5/-0.2	20.2	55	8.4 +1.5/0	14.4	7.9 - 10.9		
512 +0.020/-0.008	0.795	4.00	0.331 +0.059/-0.000	0.567	0.311 - 0.429		
13 +0.5/-0.2	20.2	100	8.4 +1.5/0	14.4	7.9 - 10.9		



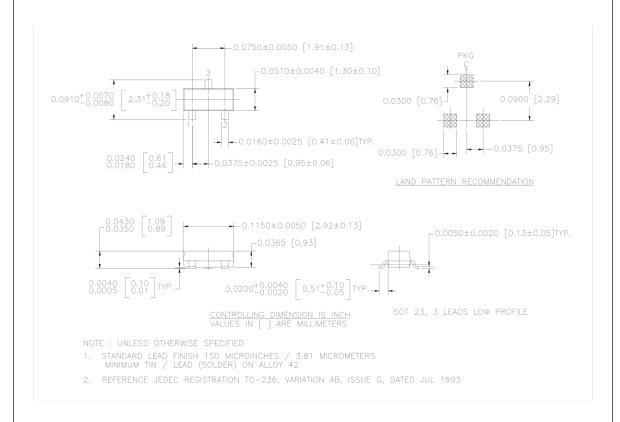
SOT-23 (FS PKG Code 49)





Scale 1:1 on letter size paper Dimensions shown below are in: inches [millimeters]

Part Weight per unit (gram): 0.0082



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FACT Quiet Series TM PACMAN TM SuperSOT TM-6 FAST $^{\circ}$ POP TM SuperSOT TM-8

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